

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

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# 2SJ350

Silicon P-Channel MOS FET

**RENESAS**

ADE-208-138 (Z)  
1st. Edition  
Aug. 1993

## Application

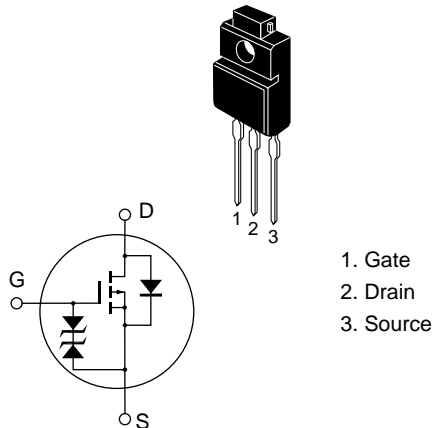
High speed power switching

## Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device can be driven from 5 V source
- Suitable for switching regulator, DC-DC converter

## Outline

TO-220FM



## Absolute Maximum Ratings (Ta = 25°C)

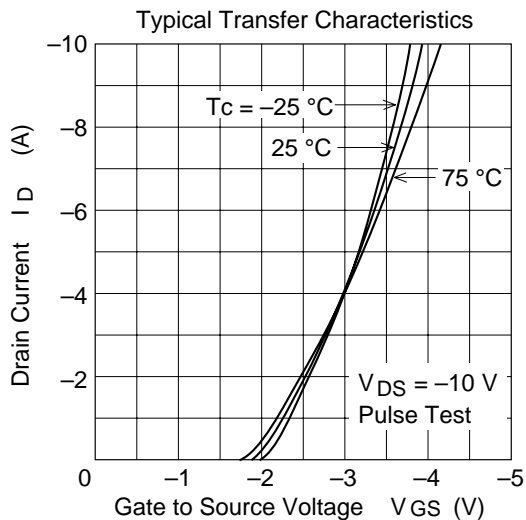
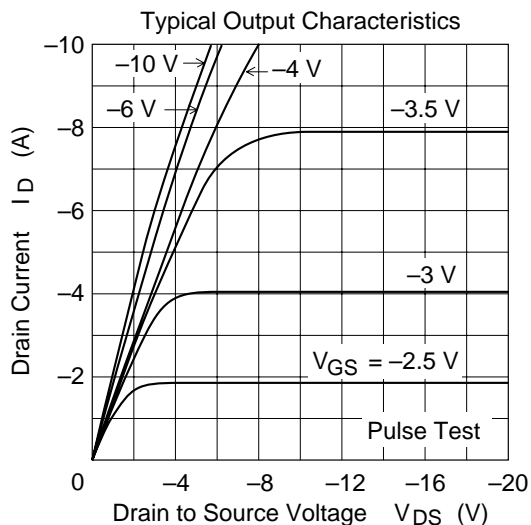
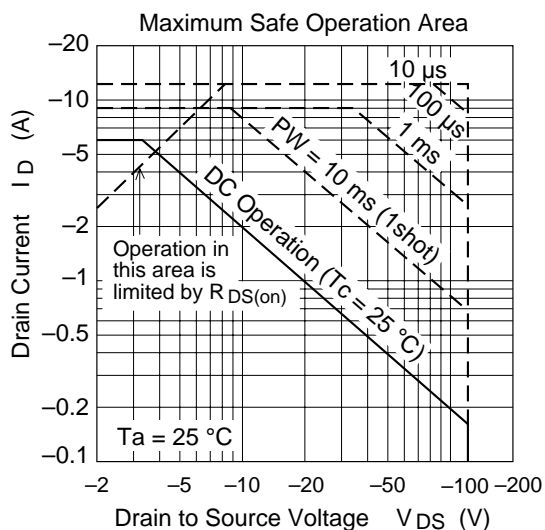
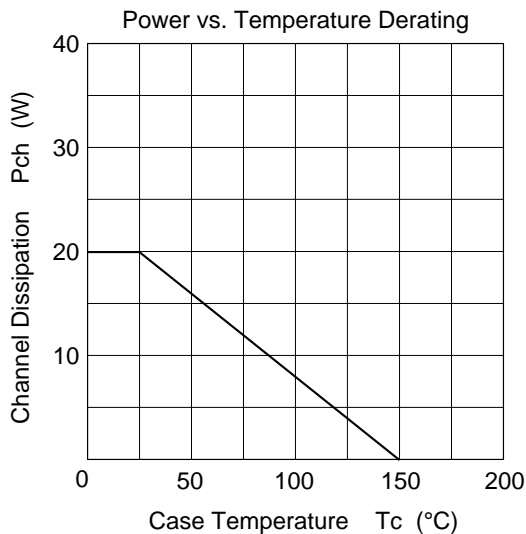
Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	-120	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	$I_D$	-6	A
Drain peak current	$I_{D(pulse)}^{*1}$	-12	A
Body to drain diode reverse drain current	$I_{DR}$	-6	A
Channel dissipation	$P_{ch}^{*2}$	20	W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

Notes: 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1\%$   
 2. Value at  $T_c = 25^\circ C$

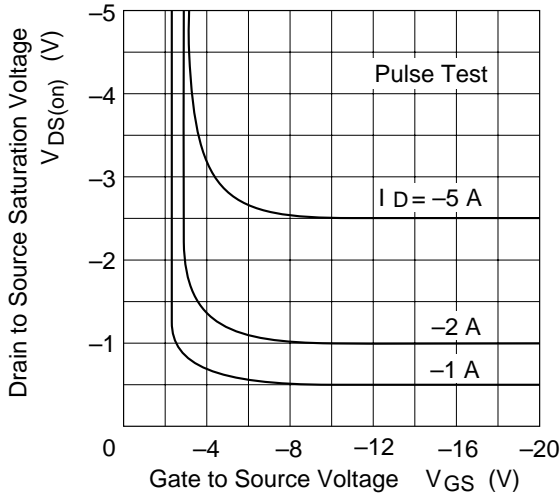
## Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-120	—	—	V	$I_D = -10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100 \mu A$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	±10	μA	$V_{GS} = \pm 16 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	-250	μA	$V_{DS} = -100 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1 \text{ mA}$ , $V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.5	0.7	Ω	$I_D = -4 \text{ A}$ , $V_{GS} = -10 \text{ V}^{*1}$
		—	0.7	0.9	Ω	$I_D = -4 \text{ A}$ , $V_{GS} = -4 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	3.0	5.0	—	S	$I_D = -4 \text{ A}$ , $V_{DS} = -10 \text{ V}^{*1}$
Input capacitance	$C_{iss}$	—	900	—	pF	$V_{DS} = -10 \text{ V}$ , $V_{GS} = 0$ ,
Output capacitance	$C_{oss}$	—	265	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	$C_{rss}$	—	65	—	pF	
Turn-on delay time	$t_{d(on)}$	—	11	—	ns	$I_D = -4 \text{ A}$ , $V_{GS} = -10 \text{ V}$ ,
Rise time	$t_r$	—	45	—	ns	$R_L = 7.5 \Omega$
Turn-off delay time	$t_{d(off)}$	—	170	—	ns	
Fall time	$t_f$	—	80	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	-1.2	—	V	$I_F = -6 \text{ A}$ , $V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	240	—	ns	$I_F = -6 \text{ A}$ , $V_{GS} = 0$ , $di_F/dt = 50 \text{ A}/\mu s$

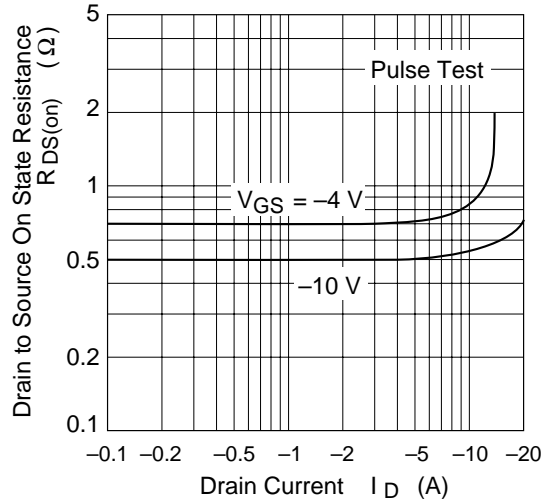
Note: 1. Pulse test



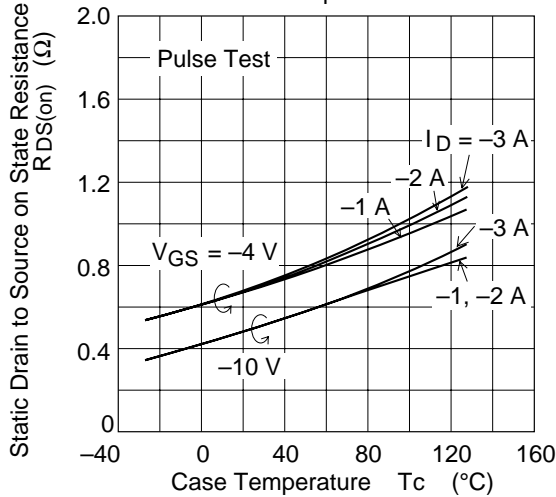
Drain to Source Saturation Voltage vs. Gate to Source Voltage



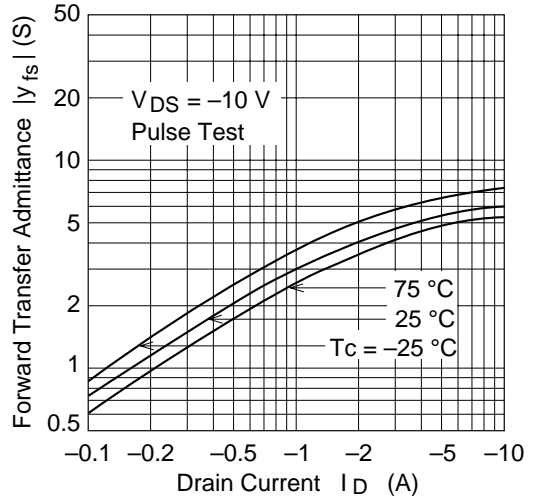
Static Drain to Source on State Resistance vs. Drain Current



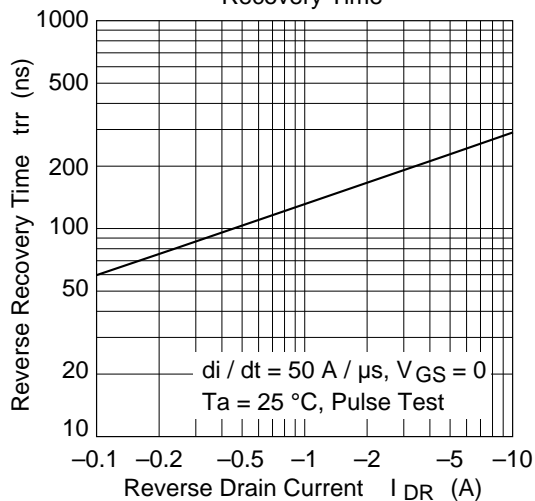
Static Drain to Source on State Resistance vs. Temperature



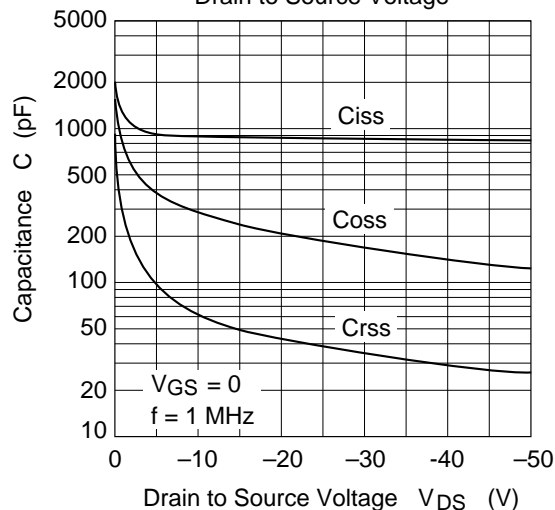
Forward Transfer Admittance vs. Drain Current



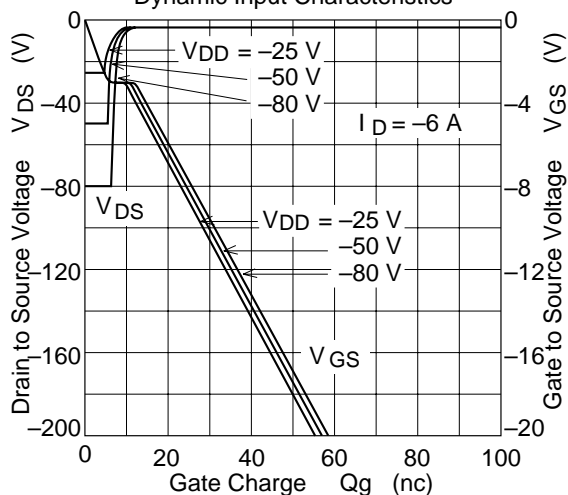
Body-Drain Diode Reverse Recovery Time



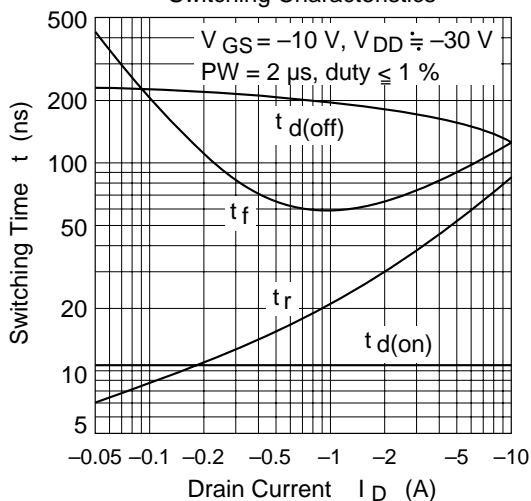
Typical Capacitance vs. Drain to Source Voltage

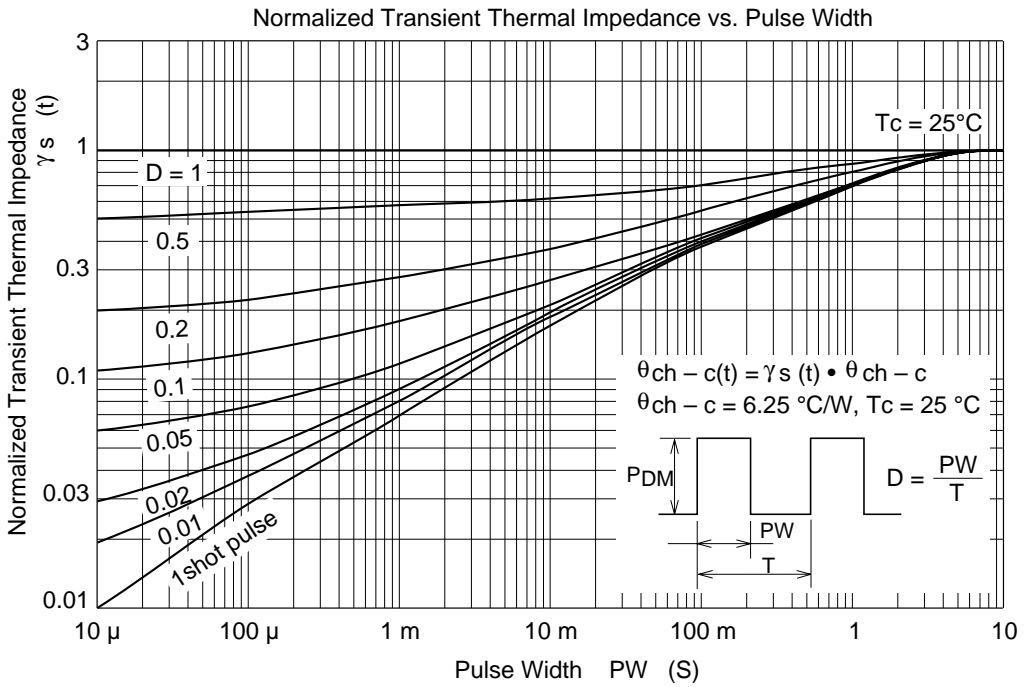
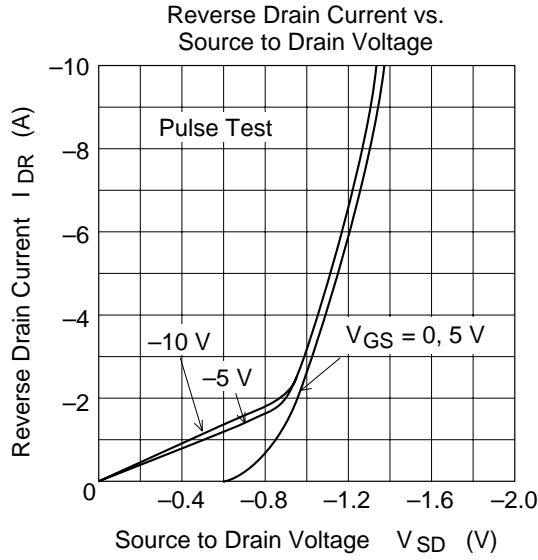


Dynamic Input Characteristics



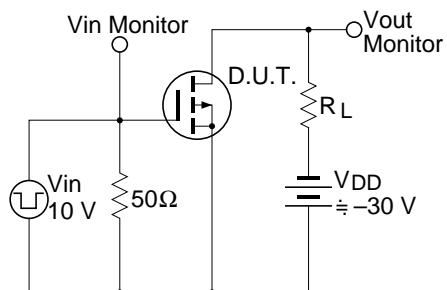
Switching Characteristics



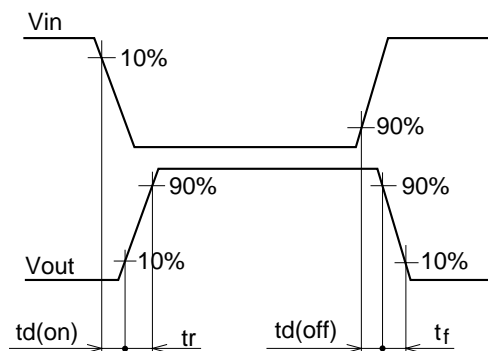




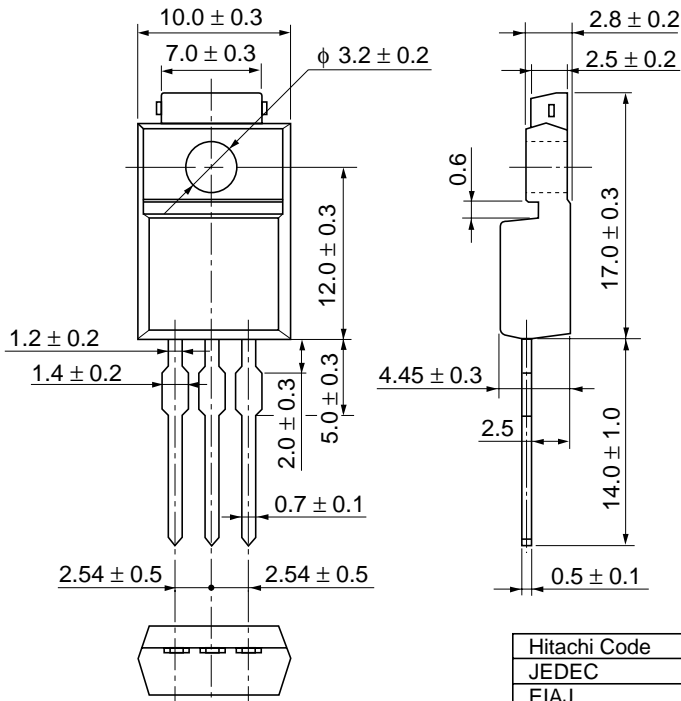
Switching Time Test Circuit



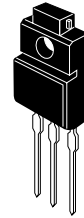
Waveforms



Package Dimensions



As of January, 2001  
Unit: mm



Hitachi Code	TO-220FM
JEDEC	—
EIAJ	Conforms
Mass (reference value)	1.8 g

## Cautions

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